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START Jic substrate. Providing depositing layer supplying atmospere including exygen Performing HD plasma Process 5106 performing HD 106e HDFECUD Process performing oxidation process 106h 106 b causing reaction creating reactive between gases oxygen species breaking Si-C bonds 108 Privomst 107 SiOz overlying SiC Johning SiDz etching depositing metal

Fig. 1

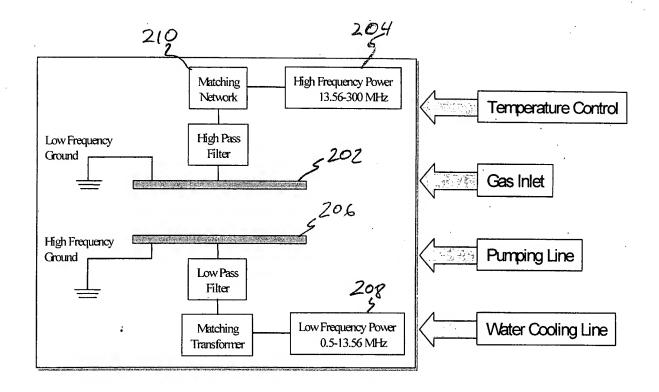


Fig. 2

Providing 5;0 substrate atmosphere including oxyge Plasma oxidation reactive oxygen species Si-c bonds 312 free Si atoms to reactive oxygen Species

Fig. 3

Sic substrate N20, and HD FECUD POLPES + reaction between sases epositing SiO2/5410

Providing SiC substrate 1502

[depositing Si layor Irsoy

[sob

[supplying atmosphere including oxygen

Performing HD oxidation process

[creating reactive oxygen species]

[solven]

[so

Fis. 5

s'ubst mosphere including HD oxidation Process reactive oxygen species between SiH4, N20, and

Fig. 6

STARTO providing Sic substrate atmosphere including oxygen HD ordation process Creating réactive oxygen species! free Si atoms to reative etching 5:02/5712 depositing F19.7

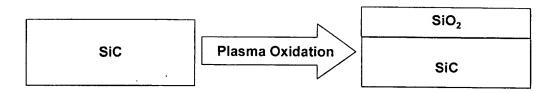


Fig. 8

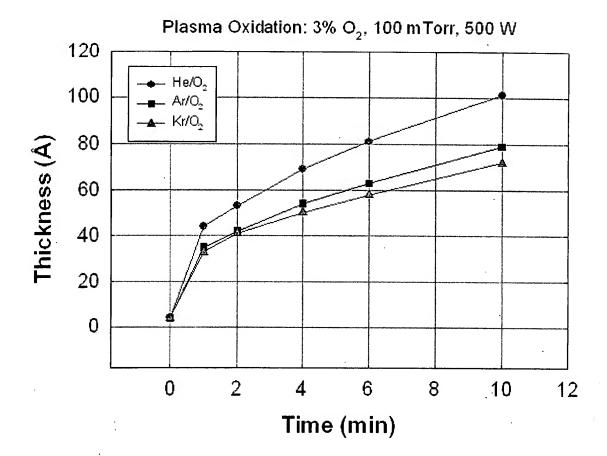


Fig. 9

HD-PECVD Deposited SiO<sub>2</sub>

SiC

Fig. 10

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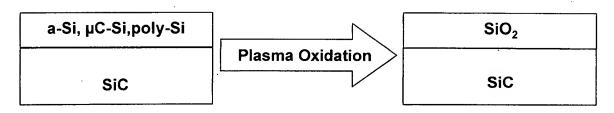


Fig. 11